10/050,426

	
IS&R	Туре
L1	L#
3	Hits
(("6458699") or ("6509239") or ("6159852")).PN.	Search Text
USPAT; US-PGPUB	DBs
2004/04/30	Time Stamp
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2	
BRS	Туре
[2	L#
45	Hits
selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or LPCVD or APCVD or chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 Cl.sub.2H.sub.2")	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30	Time Stamp
	Comme nts
	Error Definit ion
0	Er ro rs

	4	υ	
BRS	BRS	BRS	Туре
L5	L4	2	L#
2	0	1494	Hits
2 and 3	2 same 3	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or (barium-strontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or "TaO2 or "TaO2 or "TaO2 or "TaO3 or "TaO3" or "TaO3 or "TaO3" or "TaO3"))	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30 11:40	2004/04/30 11:40	2004/04/30	Time Stamp
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Type	ре L#	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definitro ion rs
				USPAT; US-PGPUB;			
	1/	25/01	crystal\$7 near5	EPO; JPO;	2004/04/30		>
OBKS	LO	17000	(dielectric or insulat\$5) DERWENT;		11:43		
				IBM_TDB			
				USPAT; US-PGPUB;			1
7 DDC	7	>		EPO; JPO;	2004/04/30		>
/ DNJ	L/	<u> </u>	2 Same o	DERWENT;	11:43		_
				IBM_TDB			
				USPAT; US-PGPUB;			
	7 0	'n		EPO; JPO;	2004/04/30		>
8 BKS	Lø	U	2 and 6	T;	11:43		<u> </u>
	***************************************			IBM_TDB			

9	
BRS	Туре
6.7	L#
1745	Hits
(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH3ub.4" or Si2H6 or "Si2H6" or "Si2H6" or "SiC12H2 or "SiC12H2 or "SiC12H2" or "SiC1sub.2H.sub.6" or SiC12H2 or "SiC1sub.2H.sub.2" or "SiC1sub.2H.sub.2" or "SiC1sub.2"	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
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			11.7/						
0			2004/04/30	EPO; JPO;	3 and 9	14	L11 14	BRS	
				USPAT; US-PGPUB;					
				IBM_TDB					
_			11:46		o same y	C	LIU	DNJ	OI
> 			2004/04/30	EPO; JPO;		>	T 10	מממ	
				USPAT; US-PGPUB;					
rs	ion rs	ш	Stamp						
ro	Definit	Ĭ		DBs	Search Text	Hits	L#	Type	
E	Error Er)							

12	
BRS	Туре
L12	# J
428	Hits
selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or LPCVD or APCVD or chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or (siH4 or "SiH4" or "SiH4 or "SiH4" or "SiH5 or "Si2H6" or "Si2H6" or "Si.sub.2 H.sub.6" or "Si.sub.2 H.sub.6" or SiC12H2 or "SiC12H2" or "SiC1.sub.2H.sub.2" or "Si C1.sub.2 H.sub.2" or "SiC1.sub.2	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30	Time Stamp
	Comme nts
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14	13	
BRS	BRS	Туре
L14	L13	L#
0	1494	Hits
12 same 13	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titan ate) or (bariumstrontium-titan ate) or ((tantalum adj cycide or dioxide or pentoxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "TaO2 or "TaO2" or "TaO.sub.2" or TaO or "TaO.sub.2" or TaO or "TaO"))	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		DBs
2004/04/30 13:58	2004/04/30	Time Stamp
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Туре	pe L#	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definitro ion rs
15 BRS	L15	7	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT:	2004/04/30 13:59		
	LIJ		12 allu 13	DERWENT; IBM_TDB	13:59		
			(crystal\$7 or mono-crystal\$7 or	USPAT; US-PGPUB;			
16 BRS	L16	136162	(mono adj crystal\$7)) with (dielectric or	EPO; JPO; DERWENT;	2004/04/30 14:02		
			insulat\$4 or oxide or dioxide or nitride)	IBM_TDB			
				USPAT; US-PGPUB;			***************************************
17 BRS	L17 21	21	12 same 16	EPO; JPO; DERWENT;	2004/04/30 14:02		
				IBM_TDB			

18	
BRS	Туре
L18	L#
16	Hits
selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit \$5) same (silane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1 or (chloro adj silane\$1 or (siH4 or "SiH4" or "Si H.sub.4" or "Si H.sub.4" or Si2H6 or "Si.sub.2H.sub.6" or "Si.sub.2H.sub.6" or "Si.sub.2H.sub.6" or SiC12H2 or "SiC12H2" or "Si C1.sub.2 H.sub.2" or "SiC1.sub.2 H.sub.2" or "SiC1.sub.2 H.sub.2" or top or ((upper or top or second) noa730 foldate\$1 Version: 1	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30	Time Stamp
	Comme nts
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23 BRS		22 BRS	21 BRS	20 BRS	19 BRS	Туре
L24	L23	L22	L21	L20	L19	De L#
158	16	29	0	16	545331	Hits
12 and 19	12 same 19	2 not 20	20 NOT 2	2 and 19	(upper or top or second) near2 (plate\$1 or electrode\$1)	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; · IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2004/04/30 15:03	2004/04/30 14:58	2004/04/30 14:31	2004/04/30 14:30	2004/04/30 14:30	2004/04/30 14:25	Time Stamp
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29	28	27	26	25	
BRS	BRS	BRS	BRS	BRS	Туре
L29	L28	L27	L26	L25	L#
27	71	44	223	10117	Hits
28 NOT 27	9 same 25	9 with 25	25 and 12	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs				
2004/04/30 15:41	2004/04/30 15:40	2004/04/30 15:40	2004/04/30 15:37	2004/04/30 15:36	Time Stamp
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0			2004/04/30 16:27	USPAT; US-PGPUB	30 or 31	21	L32	BRS	32
0			2004/04/30 16:27	USPAT; US-PGPUB	(("6013575") or ("4948755") or ("4966868") or ("5607878") or ("5663098") or ("6017823") or ("6069036") or ("5798278") or ("5798278") or ("5037778") or	10	L31	IS&R	31
0			2004/04/30 16:25	USPAT; US-PGPUB	(("4497683") or ("4963506") or ("5080933") or ("5110757") or ("5124276") or ("5364815") or ("5441012") or ("5006911") or ("5818100") or ("58187775") or ("5646073")).PN.	—	L30	IS&R	30
tro rs	Error Er Definitro ion rs	Comme Definit ro	Time Stamp	DBs	Search Text	Hits	L#	Туре	

L Number	Hits	Search Text	DB	Time stamp
1	3	(("6458699") or ("6509239") or ("6159852")).PN.	USPAT;	2004/04/30 11:04
			US-PGPUB	
2	45	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 13:56
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
1		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
1		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
,	1404	or "Si Cl.sub.2H.sub.2")	LICDAT.	2004/04/20 12:57
3	1494	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	USPAT; US-PGPUB;	2004/04/30 13:57
1		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	EPO; JPO;	
ŀ		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	IBM_TDB	
4	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:40
1	U	with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	2004/04/30 11.40
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	EPO; JPO;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (crystal\$7 with ((BST or "BST" or		
		(barium adj strontium adj titanate) or (barium-strontium-titanate) or		
		bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or	į	
1		pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or		
		"Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2"		
		or TaO or "TaO")))		
5	2	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:40
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1-or	EPO; JPO;	
1		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
l		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) and (crystal\$7 with ((BST or "BST" or		
1		(barium adj strontium adj titanate) or (barium-strontium-titanate) or		
		bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or		
		pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or		
ļ		"Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2"		
İ		or TaO or "TaO")))		
6	35621	crystal\$7 near5 (dielectric or insulat\$5)	USPAT;	2004/04/30 11:43
		,	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
7	0	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:43
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
1		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		•
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (crystal\$7 near5 (dielectric or		
	_	insulat\$5))	vvan : -	****
8	5	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 11:43
İ		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
	:	deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) and (crystal\$7 near5 (dielectric or insulat\$5))	l	

9	1745	· (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:38
l		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	
l		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЈРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")		
10	0	(crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 11:46
	ľ	(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	US-PGPUB;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	ЕРО; ЈРО;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))) same ((polysilicon or	IBM_TDB	
		poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD		
		or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or		
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
}		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2"))		
11	14	(crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 11:47
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	US-PGPUB;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	ЕРО; ЛРО;	
	ĺ	or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
	1	"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))) and ((polysilicon or	IBM_TDB	
1	1	poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD		
		or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or		
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
	}	"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or	. u .	
-		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2"))		
12	428	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 15:35
		same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor	US-PGPUB;	
		adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or	ЕРО; ЈРО;	
1		disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1)	DERWENT;	
		or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6"	IBM_TDB	
	}	or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
1		or "Si Cl.sub.2H.sub.2")		
13	1494	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or	USPAT;	2004/04/30 14:01
		"BST" or (barium adj strontium adj titanate) or	US-PGPUB;	
	1	(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	ЕРО; ЈРО;	
:		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM_TDB	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))		
14	0	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 13:58
	1	same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor	US-PGPUB;	
		adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or	ЕРО; ЈРО;	
		disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1)	DERWENT;	
		or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6"	IBM_TDB	
		or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
,		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same ((crystal\$7 or mono-crystal\$7 or (mono		
		adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj		
		titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or		
		((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5		
		or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or		
	1	"TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))		

			r	
15	7	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chloro-silane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")) and ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with ((BST or "BST" or (barium adj strontium adj titanate) or (barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.Sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 13:59
16	136162	(crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
17	21	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")) same ((crystal\$7 or mono-crystal\$7 or (mono adj crystal\$7)) with (dielectric or insulat\$4 or oxide or dioxide or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:02
18	16	selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") same ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25
19	545331	(upper or top or second) near2 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:25
20	16	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30

21	0	((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "SiC12H2" or "SiC1.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiC12H2 or "SiC12H2" or "SiC1.sub.2H.sub.2" or "Si C1.sub.2 H.sub.2" or "Si C1.sub.2H.sub.2") and ((upper or top or second) near2 (plate\$1 or electrode\$1))) NOT (selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si2H6" or "Si.sub.2H.sub.6" or "Si C1.sub.2 H.sub.2" or "SiC1.sub.2 H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:30
22	29	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2") not ((selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:31
23	16	or electrode\$1))) (selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) same ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 14:58
24	158	(selective\$3 same (polysilicon or poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) and ((upper or top or second) near2 (plate\$1 or electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:03
25	10117	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/30 15:36

		() () () () () () () () () ()	TIODAM	0004/04/00 15 05
26	223	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2004/04/30 15:37
		with (form\$4 or deposit\$5)) and (selective\$3 same (polysilicon or	US-PGPUB;	
		poly\$1 or (polycrystalline adj silicon)) same (CVD or PECVD or	ЕРО; ЈРО;	
		LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	DERWENT;	
		chemical-vapor-deposit\$5) same (silane\$1 or disilane\$1 or	IBM_TDB	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
ı		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
27	44	or "Si Cl.sub.2H.sub.2")) ((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	I ICDAT.	2004/04/30 15:40
27	44	PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	USPAT; US-PGPUB;	2004/04/30 13.40
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	EPO; JPO;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM_TDB	
			ם מו"ואפו	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1		
20	7,	or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))	IIGDAT.	2004/04/30 15:40
28	71	((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	USPAT; US-PGPUB;	2004/04/30 13.40
	, ,		EPO; JPO;	
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or	IDM_1DD	
	1	"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))		
29	27	(((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or	USPAT;	2004/04/30 15:41
29	2'	PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or	US-PGPUB;	200 110 1100 12.11
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or	ЕРО; ЛРО;	
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or	DERWENT;	
- 9		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or	IBM TDB	
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiC12H2 or "SiC12H2" or		1
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) same (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5))) NOT		
		(((polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or		
		PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5) or		
		chemical-vapor-deposit\$5) with (silane\$1 or disilane\$1 or		
		chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or		
		"SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or		
		"Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or		
		"SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2"		
		or "Si Cl.sub.2H.sub.2")) with (selective\$3 with (polysilicon or poly\$1		
		or (polycrystalline adj silicon)) with (form\$4 or deposit\$5)))		
30	11	(("4497683") or ("4963506") or ("5080933") or ("5110757") or	USPAT;	2004/04/30 16:25
		("5124276") or ("5364815") or ("5441012") or ("5006911") or	US-PGPUB	
		("5818100") or ("5037775") or ("5646073")).PN.		
31	10		USPAT;	2004/04/30 16:27
		("5663098") or ("6017823") or ("6069036") or ("5798278") or	US-PGPUB	
		("5037778") or ("5118639")).PN.		
32	21		USPAT;	2004/04/30 16:27
		("5124276") or ("5364815") or ("5441012") or ("5006911") or	US-PGPUB	
		("5818100") or ("5037775") or ("5646073")).PN.) or ((("6013575") or		
		("4948755") or ("4966868") or ("5607878") or ("5663098") or		
		("6017823") or ("6069036") or ("5798278") or ("50377778") or		
		("5118639")).PN.)	LIODAT	2002/07/12 12 00
-	3	(("6458699") or ("6509239") or ("6159852")).PN.	USPAT;	2003/07/13 12:00
	1	··	US-PGPUB	

-	431	selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	USPAT; US-PGPUB;	2004/04/30 11:38
		deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or	EPO; JPO; DERWENT;	
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6"	IBM TDB	
		or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2"	25.11_122	
		or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si		
	465444	Cl.sub.2H.sub.2")	Hanam	2002/07/12 11 40
-	465444	(upper or second or top or another) adj3 (plate\$1 or electrode\$1)	USPAT; US-PGPUB;	2003/07/13 11:40
!			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	11	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon))	USPAT;	2003/07/13 11:40
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or	US-PGPUB; EPO; JPO;	
		chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or	DERWENT;	
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6"	IBM_TDB	
:		or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2"		
		or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si Cl.sub.2H.sub.2")) with ((upper or second or top or another) adj3		
		(plate\$1 or electrode\$1))		
-	3	(("4497683") or ("5006911") or ("4963506")).PN.	USPAT;	2003/07/13 12:02
	2.5		US-PGPUB	2002/07/12 12:11
-	25	(selective\$3 with (polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	USPAT; US-PGPUB;	2003/07/13 12:11
		deposit\$5)) with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or	EPO; JPO;	
		chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or	DERWENT,	
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6"	IBM_TDB	
		or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2" or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si		
		Cl.sub.2H.sub.2")) same ((upper or second or top or another) adj3		
		(plate\$1 or electrode\$1))		
-	581471	capacitor or capacitors or DRAM or DRAMs	USPAT;	2003/07/13 12:12
			US-PGPUB; EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
-	5953	BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2003/07/13 12:14
		(barium-strontium-titanate) or bariumstrontiumtitanate	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26351	(tantalum adj (oxide or dioxide or pent-oxide)) or Ta2O5	USPAT;	2003/07/13 12:19
		or "Ta2O5" or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"	US-PGPUB; EPO; JPO;	
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	DERWENT;	
			IBM_TDB	
-	1480	(capacitor or capacitors or DRAM or DRAMs) and (BST or "BST" or	USPAT;	2003/07/13 12:43
		(barium adj strontium adj titanate) or (barium-strontium-titanate) or	US-PGPUB;	
		bariumstrontiumtitanate) and ((tantalum adj (oxide or dioxide or pentoxide or pentoxide)) or Ta2O5 or "Ta2O5" or "Ta.sub.2O.sub.5" or	EPO; JPO; DERWENT;	
}		"Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or "TaO.sub.2" or "Ta O.sub.2"	IBM TDB	
		or TaO or "TaO")	_	
-	1289	crystal\$7 with ((BST or "BST" or (barium adj strontium adj titanate) or	USPAT;	2004/04/30 11:39
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	US-PGPUB; EPO; JPO;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	DERWENT;	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO"))	IBM_TDB	

T-	615	(capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with	USPAT;	2003/07/13 12:44
		((BST or "BST" or (barium adj strontium adj titanate) or	US-PGPUB;	
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	ЕРО, ЛРО,	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM_TDB	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))		
۱ -	788		USPAT;	2003/07/13 12:45
		with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj	US-PGPUB;	
		deposit\$5))	ЕРО; ЛРО;	
			DERWENT;	
	_		IBM_TDB	
-	9	((capacitor or capacitors or DRAM or DRAMs) and (crystal\$7 with	USPAT;	2003/07/13 12:47
		((BST or "BST" or (barium adj strontium adj titanate) or	US-PGPUB;	
		(barium-strontium-titanate) or bariumstrontiumtitanate) or ((tantalum	ЕРО; ЛРО;	
		adj (oxide or dioxide or pentoxide or pent-oxide)) or Ta2O5 or "Ta2O5"	DERWENT;	
		or "Ta.sub.2O.sub.5" or "Ta.sub.2 O.sub.5" or TaO2 or "TaO2" or	IBM_TDB	
		"TaO.sub.2" or "Ta O.sub.2" or TaO or "TaO")))) and (selective\$3 with		
		(polysilicon or poly\$1 or (polycrystalline adj silicon)) with (CVD or PECVD or LPCVD or APCVD or (chemical adj vapor adj deposit\$5))		
		with (silicon or silane\$1 or disilane\$1 or chlorosilane\$1 or		
		chloro-silane\$1 or (chloro adj silane\$1) or SiH4 or "SiH4" or		
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6"		
1		or "Si.sub.2 H.sub.6" or SiCl2H2 or "SiCl2H2" or "SiCl.sub.2H.sub.2"		
		or "Si Cl.sub.2 H.sub.2" or "SiCl.sub.2 H.sub.2" or "Si		
		Cl.sub.2H.sub.2"))		